

HIGH SPEED SWITCHING APPLICATION.

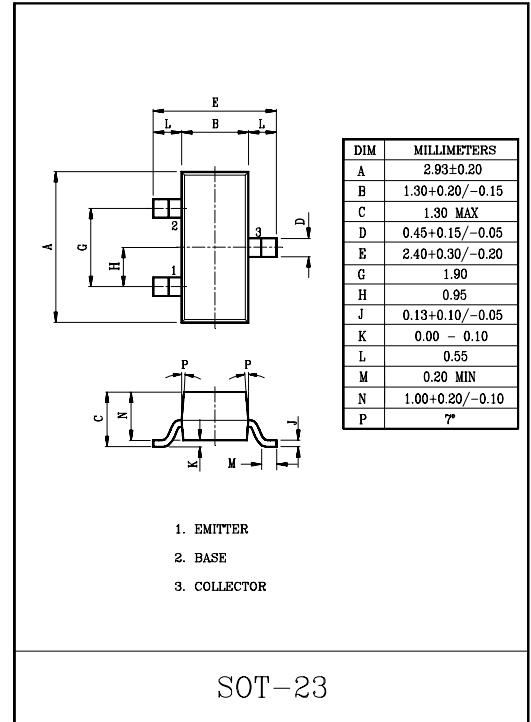
FEATURES

- Excellent High Frequency Characteristics.
- Excellent Switching Characteristics.

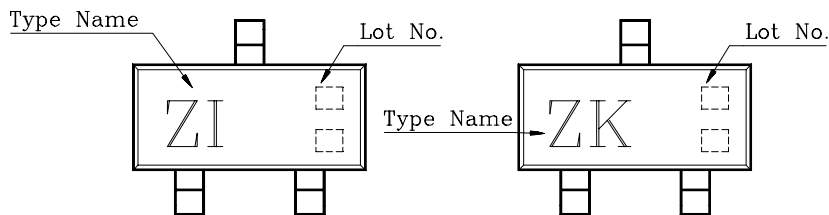
MAXIMUM RATINGS(Ta=25°C)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Collector-Base Voltage	V _{CBO}	40	V
Collector-Emitter Voltage	V _{CEO}	15	V
Emitter-Base Voltage	V _{EBO}	4.5	V
Collector Current	I _C	500	mA
Collector Power Dissipation (Ta=25°C)	* P _C	350	mW
Junction Temperature	T _j	150	°C
Storage Temperature Range	T _{stg}	-55~150	°C

* Package Mounted On 99.5% Alumina 10x8x0.6mm



Marking



MARK SPEC

TYPE	MARK
KTN2369S	Z I
KTN2369AS	Z K

KTN2369S/AS

ELECTRICAL CHARACTERISTICS (Ta=25°C)

CHARACTERISTIC		SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector Cut-off Current		I _{CBO}	V _{CB} =20V, I _E =0	-	-	0.4	μA
			V _{CB} =20V, I _E =0, Ta=125°C	-	-	30	
Collector-Base Breakdown Voltage		V _{(BR)CBO}	I _C =10μA, I _E =0	40	-	-	V
Collector-Emitter Breakdown Voltage *		V _{(BR)CEO}	I _C =10mA, I _B =0	15	-	-	
Emitter-Base Breakdown Voltage		V _{(BR)EBO}	I _E =10μA, I _C =0	4.5	-	-	
DC Current Gain *	KTN2369S	h _{FE}	I _C =10mA, V _{CE} =1.0V	40	-	120	
	KTN2369AS			-	-	120	
	KTN2369S		I _C =10mA, V _{CE} =1.0V, Ta=-55°C	20	-	-	
	KTN2369AS		I _C =10mA, V _{CE} =0.35V, Ta=-55°C	20	-	-	
	KTN2369AS		I _C =100mA, V _{CE} =2.0V	20	-	-	
	KTN2369S		I _C =100mA, V _{CE} =20V	20	-	-	
Collector-Emitter Saturation Voltage *		V _{CE(sat)}	I _C =10mA, I _B =1.0mA	-	-	0.25	V
Base-Emitter Saturation Voltage *		V _{BE(sat)}	I _C =10mA, I _B =1.0mA	0.70	-	0.85	V
Collector Output Capacitance		C _{ob}	V _{CB} =5.0V, I _E =0, f=1.0MHz	-	-	4.0	pF
Storage Time	KTN2369AS	t _{stg}	I _C =100mA, I _{B1} =-I _{B2} =10mA, V _{CC} =10V	-	-	13	nS
Turn-on Time		t _{on}	I _C =10mA, I _{B1} =3.0mA, V _{CC} =3.0V, I _{B2} =-1.5mA	-	-	12	
Turn-off Time	KTN2369AS	t _{off}	I _C =10mA, I _{B1} =3.0mA, I _{B2} =-1.5mA, V _{CC} =3.0V	-	-	15	

*Pulse Test : Pulse Width ≤ 300μS, Duty Cycle ≤ 2.0%